EE 716 Midterm Exam (2018 Spring)

09:00-10:20, 05/15/2018, Prof. Jinsang Kim

Assume that a matched unit inverter has widths of 50nm for nMOS and 100nm for pMOS, respectively. The 50nm process technology uses the followings unless stated otherwise: $V_{DD}=1~V,~Vto=0.3~V,~\beta_n=1mA/~V^2,~\Phi_s=0.6~V,~\gamma=0.3~V^{0.5},~\lambda=0.02,~\tau=3RC=3ps,$ electron velocity = $10^5 cm/s$

1. (10pts) The following netlist is an output of a cell-based design methodology. Decide the design step which produces the following netlist. What is your criteria for your decision?

- 2. (14pts) Design a scannable negative edge sensitive D-type FF at the transistor level.
- **3.** (36pts) Given Y = AB + C, We should design the circuits using CMOS logic, pseudo-nMOS logic and domino logic, respectively. Please try to design a perfect circuit as possible. The signal 'A' arrives later than the signal 'B'.
- a) design the transistor-level circuits of each logic
- b) decide the transistor sizes of each logic
- c) estimate the logical effort of the signal 'A' for each logic

	setup time	clk-to-Q delay	D-to-Q delay	Contamination delay	hold time	clock skew
FFs	60 ps	45 ps	-	30 ps	25 ps	50 ps
latches	20 ps	45 ps	35	30 ps	25 ps	50 ps

- 4. (30pts) For each of the following sequencing styles, determine the minimum logic contamination delay in each clock cycle (or half-cycle for two-phase latches) of 500 ps.
- a) FFs
- b) two-phase latches with 40 ps of nonoverlap between phases
- c) pulsed latches with 80 ps pulse width
- 5. (10pts) In the case of 4.b), what is the maximum time borrowing of the first combinational logic.